



PJM05P30PA

P-Channel Enhancement Mode Power MOSFET

Features

- High density cell design for ultra low $R_{DS(on)}$
- Advanced trench technology
- $V_{DS} = -30V, I_D = -5.1A$
 $R_{DS(on)} < 55m\Omega @ V_{GS} = -10V$

Applications

- PWM applications
- Load switch
- Power management

Absolute Maximum Ratings

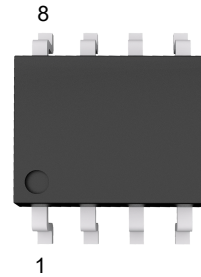
Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$-V_{DS}$	30	V
Gate-Source Voltage	$-V_{GS}$	± 20	V
Drain Current-Continuous	$-I_D$	5.1	A
Drain Current-Pulsed ^{Note1}	$-I_{DM}$	20.4	A
Maximum Power Dissipation	P_D	2.15	W
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

Thermal Characteristics

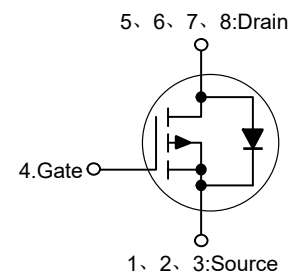
Thermal Resistance, Junction-to-Ambient ^{Note2}	$R_{\theta JA}$	58	°C/W
--	-----------------	----	------

SOP-8



Marking code: 9435

Schematic Diagram





PJM05P30PA

P-Channel Enhancement Mode Power MOSFET

Electrical Characteristics

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$-V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	30	--	--	V
Zero Gate Voltage Drain Current	$-I_{DSS}$	$V_{DS}=-30V, V_{GS}=0V$	--	--	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	--	--	± 100	nA
Gate Threshold Voltage ^{Note3}	$-V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	1	1.5	2.5	V
Drain-Source On-Resistance ^{Note3}	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-5.1A$	--	43	55	m Ω
		$V_{GS}=-4.5V, I_D=-4.2A$	--	65	90	m Ω
Forward Transconductance ^{Note3}	g_{FS}	$V_{DS}=-5V, I_D=-4A$	--	7.5	--	S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=-15V, V_{GS}=0V, f=1MHz$	--	596	--	pF
Output Capacitance	C_{oss}		--	95	--	pF
Reverse Transfer Capacitance	C_{rss}		--	68	--	pF
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-15V, V_{GS}=-10V$ $I_D=-1A, R_{GEN}=2.5\Omega$	--	14	--	nS
Turn-on Rise Time	t_r		--	61	--	nS
Turn-off Delay Time	$t_{d(off)}$		--	19	--	nS
Turn-off Fall Time	t_f		--	10	--	nS
Total Gate Charge	Q_g	$V_{DS}=-15V, V_{GS}=-10V$ $I_D=-5.1A$	--	6.8	--	nC
Gate-Source Charge	Q_{gs}		--	1	--	nC
Gate-Drain Charge	Q_{gd}		--	1.4	--	nC
Source-Drain Diode Characteristics						
Diode Forward Voltage ^{Note3}	$-V_{SD}$	$V_{GS}=0V, I_S=-5.1A$	--	0.8	1.2	V
Diode Forward Current ^{Note2}	$-I_S$		--	--	5.1	A

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \leq 10$ sec.

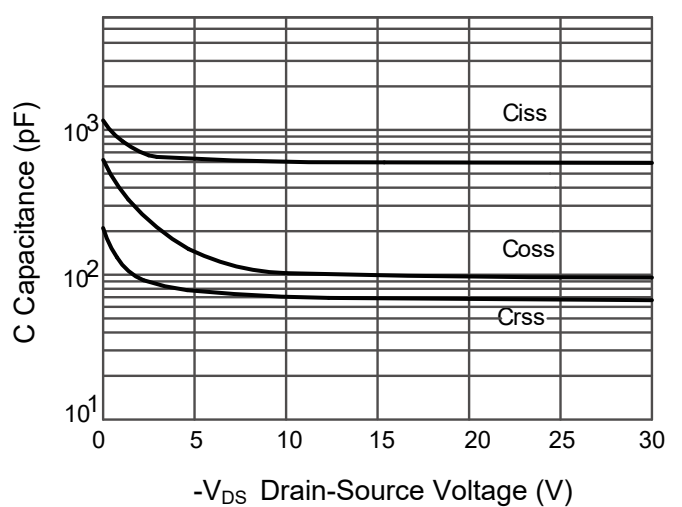
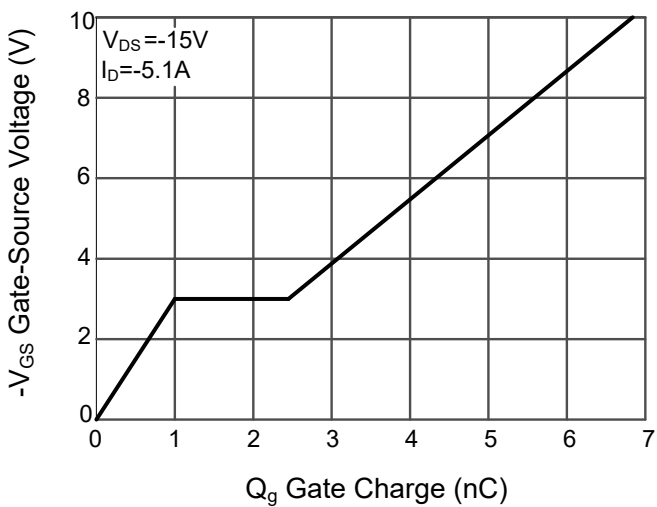
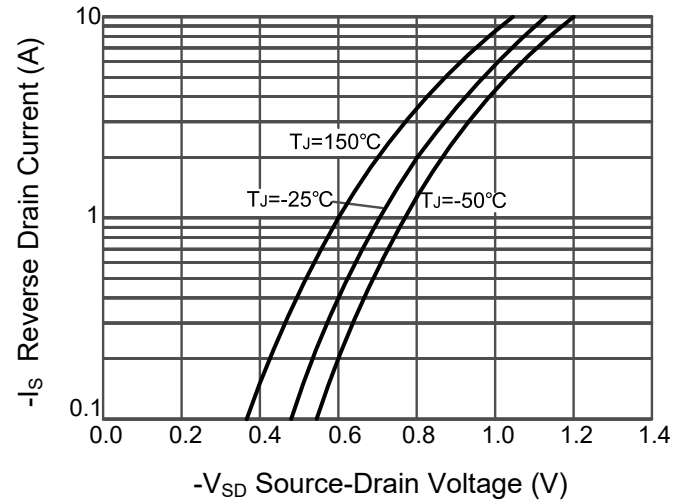
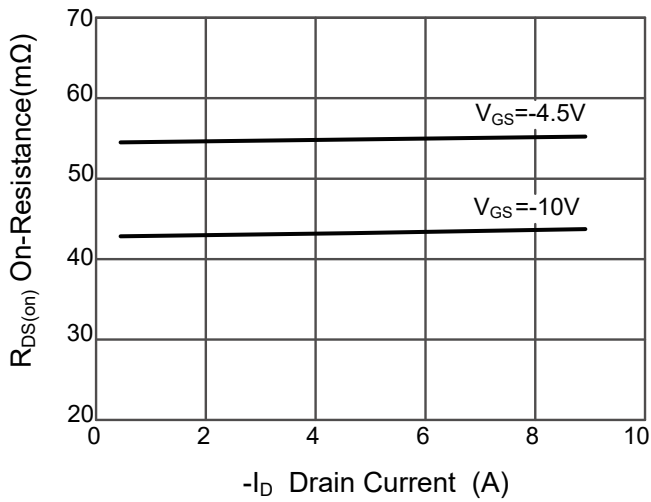
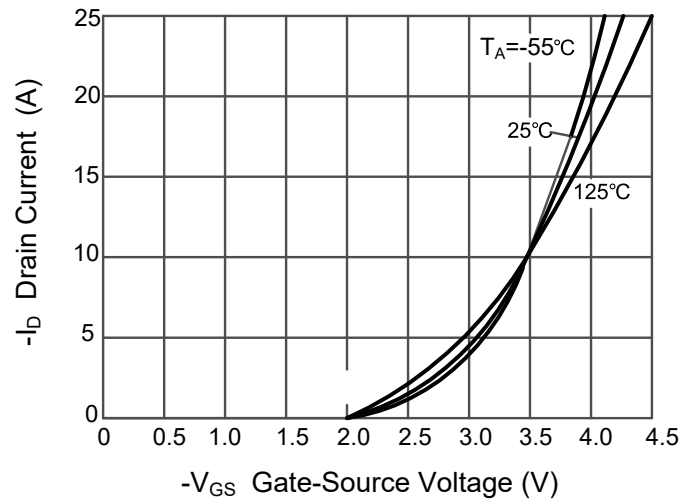
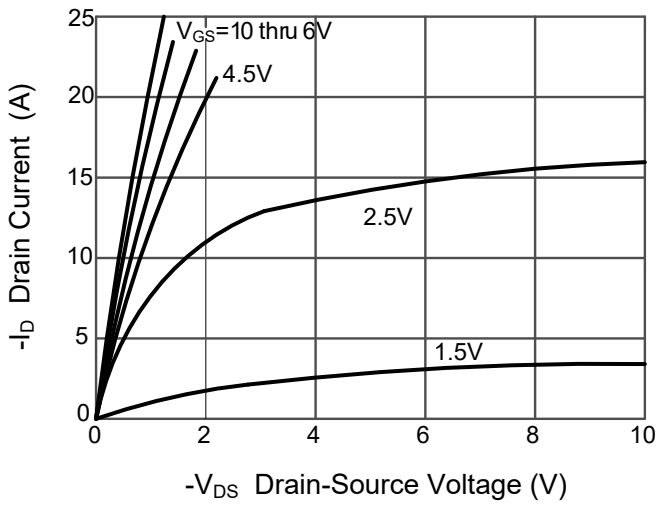
3. Pulse Test: Pulse width $\leq 300\mu s$, duty cycles $\leq 2\%$



PJM05P30PA

P-Channel Enhancement Mode Power MOSFET

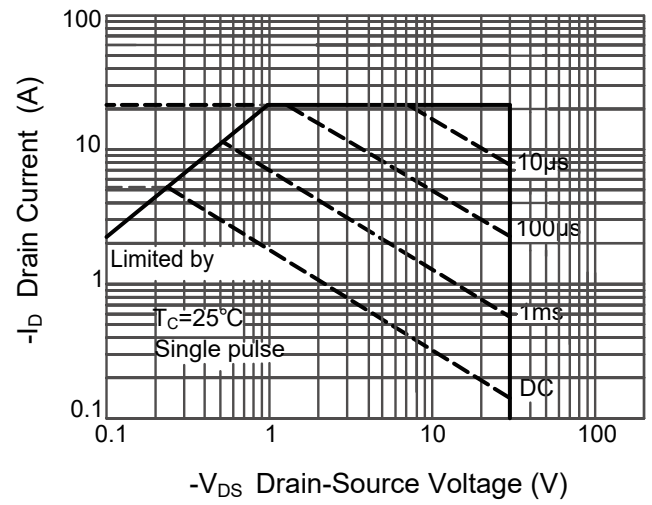
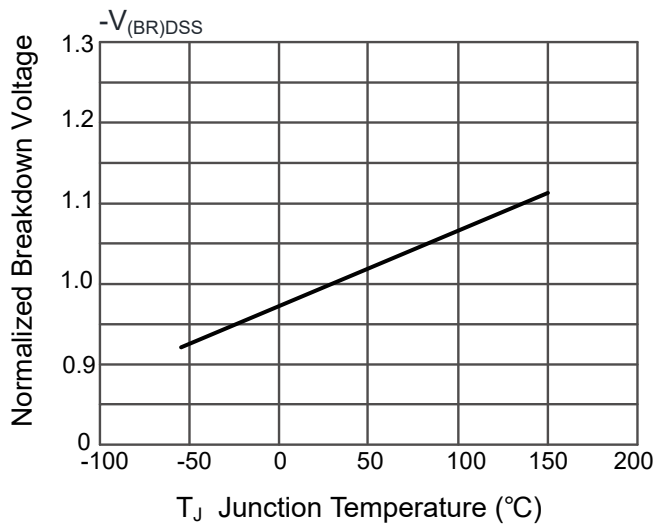
Typical Characteristic Curves





PJM05P30PA

P-Channel Enhancement Mode Power MOSFET





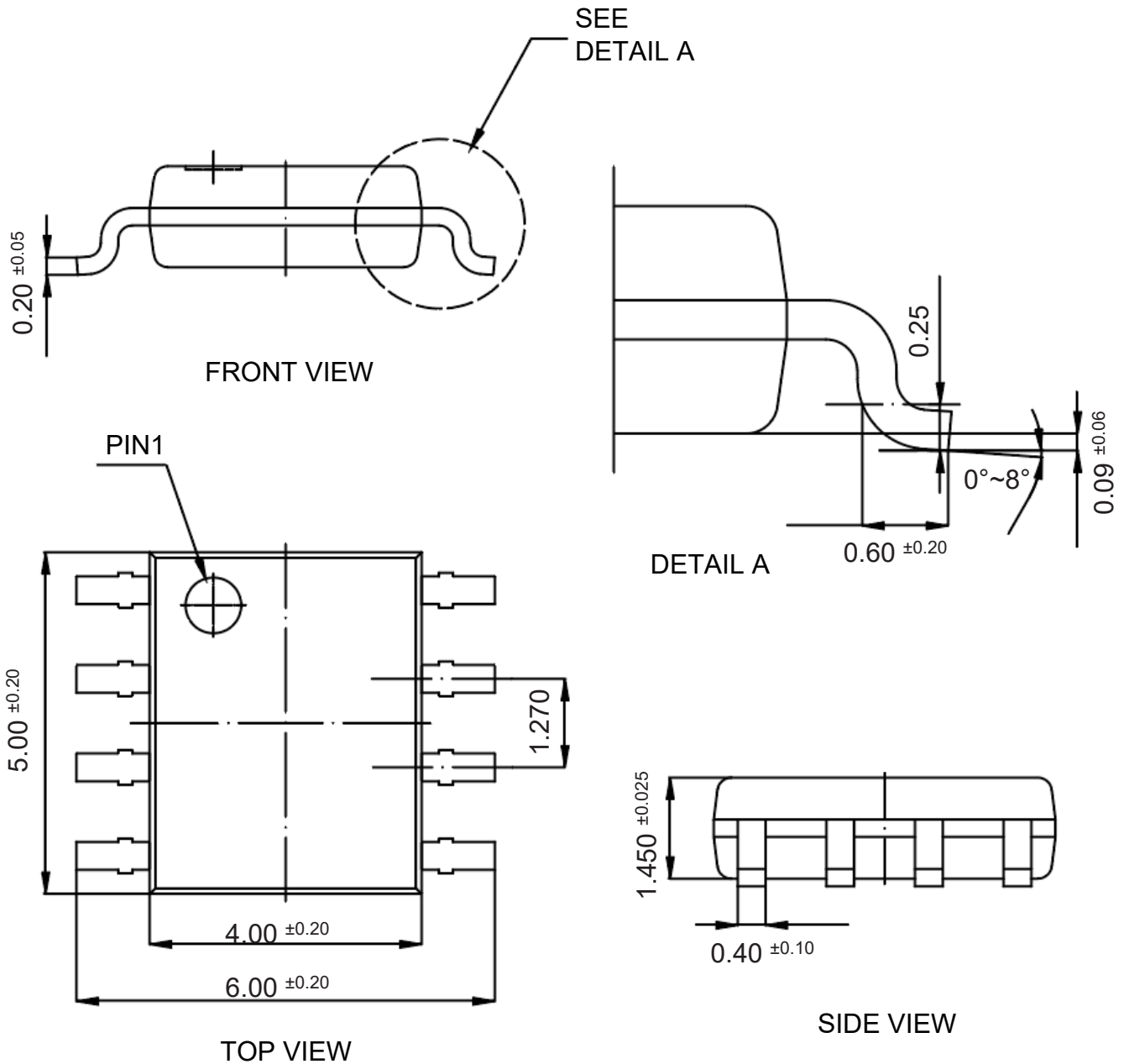
PJM05P30PA

P-Channel Enhancement Mode Power MOSFET

Package Outline

SOP-8

Dimensions in mm



Ordering Information

Device	Package	Shipping
PJM05P30PA	SOP-8	4,000PCS/Reel&13inches